

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	22	(method and semiconductor and device and form and first and second and gate and electrode and (insulat\$3 or dielectric) and (layer or film) and source and drain and organic and material and etch).clm.	US-PGPUB; USPAT; USOCR	OR	ON	2009/06/09 13:20

6/9/2009 2:07:49 PM

C:\Documents and Settings\aho1\My Documents\EAST\Workspaces\10573328.wsp